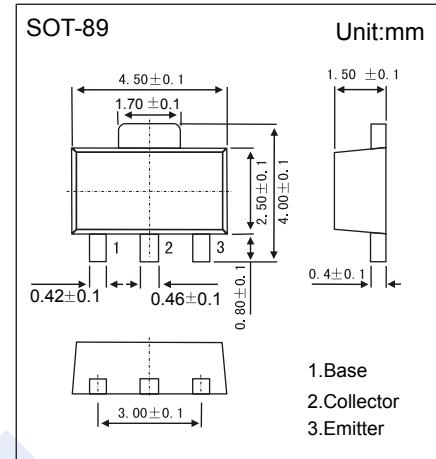


PNP Transistors

2SA1724

■ Features

- Collector Current Capability $I_C = -0.3A$
- Collector Emitter Voltage $V_{CE0} = -20V$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-30	V
Collector - Emitter Voltage	V_{CEO}	-20	
Emitter - Base Voltage	V_{EBO}	-3	
Collector Current - Continuous	I_C	-300	mA
Collector Current - Pulse	I_{CP}	-600	
Collector Power Dissipation (Note.1)	P_C	500	mW
		1.3	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1: Mounted on ceramic substrate ($250mm^2 \times 0.8mm^1$)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -100 \mu A, I_E = 0$	-30			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-20			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-3			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -2V, I_C = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 mA, I_B = -10mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -50mA$	15		100	
		$V_{CE} = -5V, I_C = -300mA$	5			
Collector output capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		4.9		pF
Reverse Transfer capacitance	C_{re}	$V_{CB} = -10V, f = 1MHz$		4.4		
Transition frequency	f_T	$V_{CE} = -5V, I_C = -100mA$		1.5		GHz

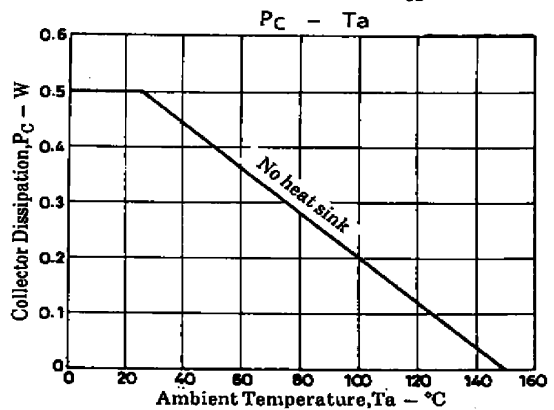
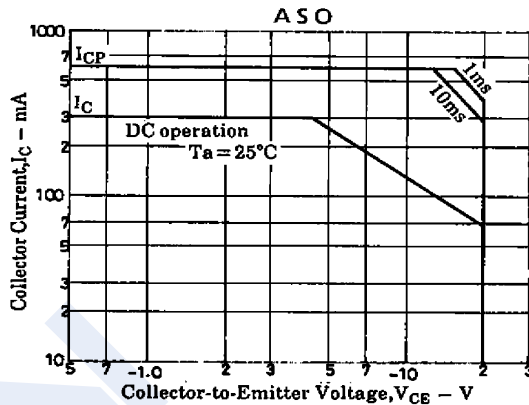
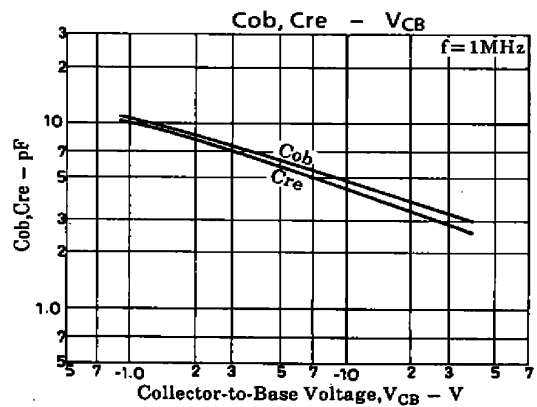
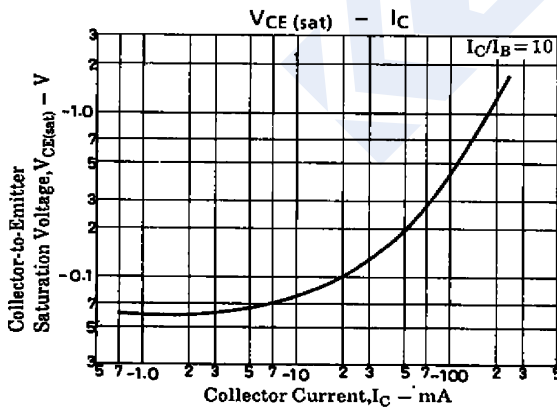
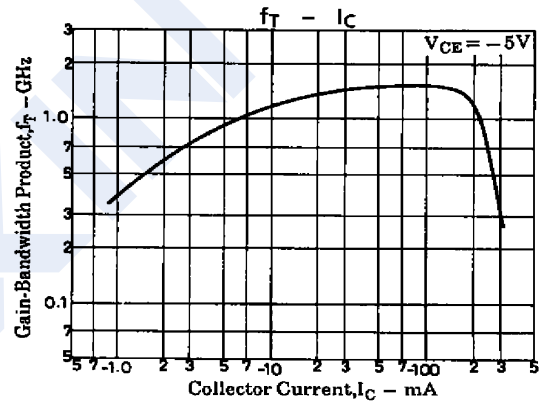
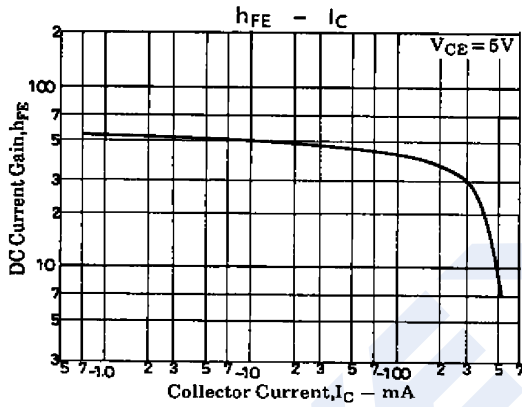
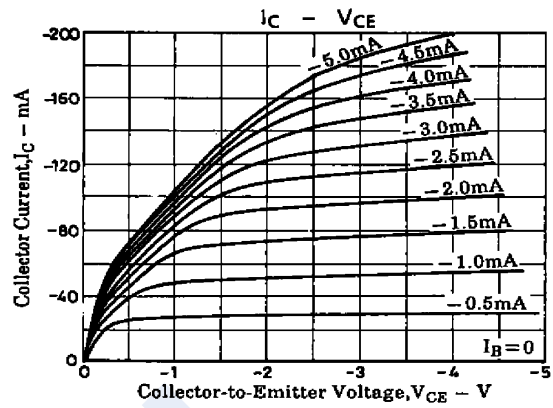
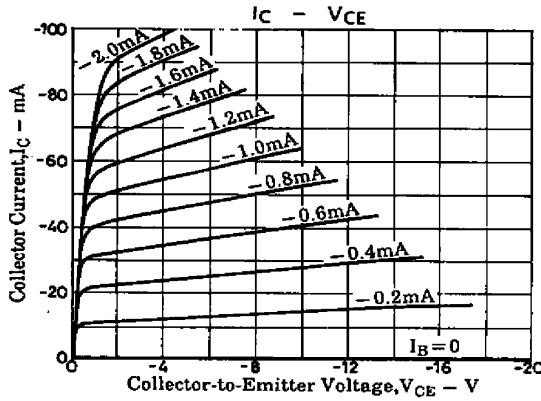
■ Marking

Marking	AJ
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■ Typical Characteristics



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■ Typical Characteristics

